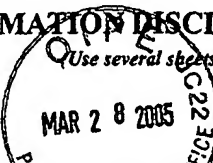


INFORMATION DISCLOSURE CITATION (Use several sheets if necessary) 	Docket number (Optional) 15436.442.6	Application Number 10/781,446
	Applicant(s) Bo Su Chen	
	Filing Date 02/17/2004	Group Art Unit 2874 2883

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>[initials]</i>		6,536,959	03/2003	Kuhn, et al.			
<i>[initials]</i>		3,271,631	09/1966	J. C. Marinace			
<i>[initials]</i>		3,936,742	02/1976	Krause			
<i>[initials]</i>		4,408,871	10/1983	Kojima			
<i>[initials]</i>		4,490,618	12/1984	Cielo			
<i>[initials]</i>		4,678,269	07/1987	Pace			
<i>[initials]</i>		4,681,414	07/1987	Hershet			
<i>[initials]</i>		4,755,036	07/1988	Suzuki, et al.			
<i>[initials]</i>		4,765,703	08/1988	Suzuki, et al.			
<i>[initials]</i>		4,816,912	03/1989	Suzuki, et al.			
<i>[initials]</i>		4,818,058	04/1995	Bonanni			
<i>[initials]</i>		4,829,537	05/1989	Baer			
<i>[initials]</i>		4,842,390	06/1989	Sottini, et al.			
<i>[initials]</i>		4,894,785	01/1990	Fernandes			
<i>[initials]</i>		4,935,029	06/1990	Matsutani, et al.			
<i>[initials]</i>		4,943,128	07/1990	Takada, et al.			
<i>[initials]</i>		4,976,727	12/1990	Matsutani, et al.			
<i>[initials]</i>		5,001,323	03/1991	Matsutani, et al.			
<i>[initials]</i>		5,029,101	07/1991	Fernandes			
<i>[initials]</i>		5,029,973	07/1991	Rink			
<i>[initials]</i>		5,047,076	09/1991	Cagnolato, et al.			
<i>[initials]</i>		5,170,406	12/1992	Tidwell			
<i>[initials]</i>		5,312,398	05/1994	Hobart, et al.			
<i>[initials]</i>		5,354,323	10/1994	Whitebook			
<i>[initials]</i>		5,400,145	03/1995	Suita, et al.			
<i>[initials]</i>		5,402,258	03/1995	Murakami, et al.			
<i>[initials]</i>		5,404,869	04/1995	Parkyn, Jr., et al.			
<i>[initials]</i>		5,414,600	05/1995	Strobl, et al.			
<i>[initials]</i>		5,415,652	05/1995	Mueller, et al.			
<i>[initials]</i>		5,430,634	07/1995	Baker, et al.			
<i>[initials]</i>		5,458,594	10/1995	Mueller, et al.			
<i>[initials]</i>		5,467,104	11/1995	Burnes, III et al.			
EXAMINER <i>Ryan J. Galt</i>	DATE CONSIDERED <i>6/21/05</i>						

EXAMINER: Initial of citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>	Docket number (Optional) 15436.442.6	Application Number 10/781,446
	Applicant(s) Bo Su Chen	
	Filing Date 02/17/2004	Group Art Unit 2874 2883

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>h</i>		5,470,314	11/1995	Walimsky			
<i>R</i>		5,491,344	02/1996	Kenny, et al.			
<i>R</i>		5,495,576	02/1996	Ritchey			
<i>R</i>		5,509,095	04/1996	Baker, et al.			
<i>R</i>		5,530,709	06/1996	Waarts, et al.			
<i>R</i>		5,577,492	11/1996	Parkyn, Jr. et al.			
<i>R</i>		5,594,752	01/1997	Endriz			
<i>R</i>		5,596,339	01/1997	Furness, III et al.			
<i>R</i>		5,600,126	02/1997	Appel, et al.			
<i>R</i>		5,613,769	03/1997	Parkyn, Jr. et al.			
<i>R</i>		5,659,327	08/1997	Furness, III et al.			
<i>R</i>		5,676,453	10/1997	Parkyn, Jr. et al.			
<i>R</i>		5,677,920	10/1997	Waarts, et al.			
<i>R</i>		5,773,817	06/1998	Kingsley, et al.			
<i>R</i>		5,777,342	07/1998	Baer			
<i>R</i>		5,790,576	08/1998	Waarts, et al.			
<i>R</i>		5,793,783	08/1998	Endriz			
<i>R</i>		5,799,543	09/1998	Nagai, et al.			
<i>R</i>		5,802,092	09/1998	Endriz			
<i>R</i>		5,806,955	09/1998	Parkyn, Jr. et al.			
<i>R</i>		5,832,055	11/1998	Dewaele			
<i>R</i>		5,836,667	11/1998	Baker, et al.			
<i>R</i>		5,861,995	01/1999	Gordon			
<i>R</i>		5,866,911	02/1999	Baer			
<i>R</i>		5,936,777	08/1999	Dempewolf			
<i>R</i>		5,952,668	09/1999	Baer			
<i>R</i>		5,993,466	11/1999	Yoon			
<i>R</i>		5,993,467	11/1999	Yoon			
<i>R</i>		5,998,215	12/1999	Prather, et al.			
<i>R</i>		6,008,781	12/1999	Furness, III et al.			
<i>R</i>		6,075,650	06/2000	Morris, et al.			
<i>R</i>		6,139,517	10/2000	Macoviak			

EXAMINER <i>Dez Long</i>	DATE CONSIDERED <i>6/21/05</i>
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>	Docket number (Optional)	Application Number
	15436.442.6	10/781,446
	Applicant(s)	
	Bo Su Chen	
	Filing Date	Group Art Unit
	02/17/2004	2874 2883

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>Mr</i>		6,160,916	12/2000	Horiuchi			
<i>Mr</i>		6,186,648	02/2001	Baker, et al.			
<i>Mr</i>		6,222,864	04/2001	Waarts, et al.			
<i>Mr</i>		6,254,563	07/2001	Macoviak, et al.			
<i>Mr</i>		6,259,104	07/2001	Baer			
<i>Mr</i>		6,317,103	11/2001	Furness, III et al.			
<i>Mr</i>		6,324,326	11/2001	Dejneka, et al.			
<i>Mr</i>		6,349,159	02/2002	Uebbing, et al.			
<i>Mr</i>		6,356,572	03/2002	Tanaka, et al.			
<i>Mr</i>		6,366,338	04/2002	Masubuchi, et al.			
<i>Mr</i>		6,410,213	06/2002	Raguin, et al.			
<i>Mr</i>		6,411,835	06/2002	Modell, et al.			
<i>Mr</i>		4,317,085	02/23/1982	Brunham, et al.			
<i>Mr</i>		4,466,694	08/21/1984	MacDonald			
<i>Mr</i>		4,660,207	04/21/1987	Svilans			
<i>Mr</i>		4,675,058	06/23/1987	Plaster			
<i>Mr</i>		4,784,722	11/15/1988	Liau, et al.			
<i>Mr</i>		4,885,592	12/05/1989	Kofol, et al.			
<i>Mr</i>		4,901,327	02/13/1990	Bradley			
<i>Mr</i>		4,943,970	07/24/1990	Bradley			
<i>Mr</i>		4,956,844	09/11/1990	Goodhue, et al.			
<i>Mr</i>		5,031,187	07/09/1991	Orenstein, et al.			
<i>Mr</i>		5,052,016	09/24/1991	Mahbobzadeh			
<i>Mr</i>		5,056,098	10/08/1991	Anthony, et al.			
<i>Mr</i>		5,062,115	10/29/1991	Thornton			
<i>Mr</i>		5,068,869	11/26/1991	Wang, et al.			
<i>Mr</i>		5,079,774	01/07/1992	Mendez, et al.			
<i>Mr</i>		5,115,442	05/19/1992	Lee, et al.			
<i>Mr</i>		5,117,469	05/26/1992	Cheung, et al.			
<i>Mr</i>		5,140,605	08/18/1992	Paoli, et al.			
<i>Mr</i>		5,157,537	10/20/1992	Rosenblatt, et al.			
<i>Mr</i>		5,158,908	10/27/1992	Blonder, et al.			

EXAMINER	DATE CONSIDERED
<i>Ryan Sp86</i>	<i>6/16/02</i>

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>	Docket number (Optional) 15436.442.6	Application Number 10/781,446
	Applicant(s) Bo Su Chen	
	Filing Date 02/17/2004	Group Art Unit 2874 2883

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>Ch</i>		5,212,706	05/18/1993	Jain			
<i>Ch</i>		5,216,263	06/01/1993	Paoli			
<i>Ch</i>		5,216,680	06/01/1993	Magnusson, et al.			
<i>Ch</i>		5,237,581	08/17/1993	Asada, et al.			
<i>Ch</i>		5,245,622	09/14/1993	Jewell, et al.			
<i>Ch</i>		5,258,990	11/02/1993	Olbright, et al.			
<i>Ch</i>		5,262,360	11/16/1993	Holonyak, Jr. et al.			
<i>Ch</i>		5,285,466	02/08/1994	Tabatabaie			
<i>Ch</i>		5,293,392	03/08/1994	Shieh, et al.			
<i>Ch</i>		5,317,170	05/31/1994	Paoli			
<i>Ch</i>		5,317,587	05/31/1994	Ackley, et al.			
<i>Ch</i>		5,325,386	06/28/1994	Jewell, et al.			
<i>Ch</i>		5,331,654	07/19/1994	Jewell, et al.			
<i>Ch</i>		5,337,074	08/09/1994	Thornton			
<i>Ch</i>		5,337,183	08/09/1994	Rosenblatt, et al.			
<i>Ch</i>		5,349,599	09/20/1994	Larkins			
<i>Ch</i>		5,351,256	09/27/1994	Schneider, et al.			
<i>Ch</i>		5,359,447	10/25/1994	Hahn, et al.			
<i>Ch</i>		5,359,618	10/25/1994	Lebby, et al.			
<i>Ch</i>		5,363,397	11/08/1994	Collins, et al.			
<i>Ch</i>		5,373,520	12/13/1994	Shoji, et al.			
<i>Ch</i>		5,373,522	12/13/1994	Holonyak, Jr., et al.			
<i>Ch</i>		5,376,580	12/27/1994	Kish, et al.			
<i>Ch</i>		5,386,426	01/31/1995	Stephens			
<i>Ch</i>		5,390,209	02/14/1995	Vakhshoori			
<i>Ch</i>		5,396,508	03/17/1995	Bour, et al.			
<i>Ch</i>		5,404,373	04/04/1995	Cheng			
<i>Ch</i>		5,412,678	05/02/1995	Treat, et al.			
<i>Ch</i>		5,412,680	05/02/1995	Swirham, et al.			
<i>Ch</i>		5,416,044	05/16/1995	Chino, et al.			
<i>Ch</i>		5,428,634	06/27/1995	Bryan, et al.			
<i>Ch</i>		5,438,584	08/01/1995	Paoli, et al.			

EXAMINER <i>Ryan J. Gabe</i>	DATE CONSIDERED <i>6/24/05</i>
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INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)	Docket number (Optional) 15436.442.6	Application Number 10/781,446
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	Filing Date 02/17/2004	Group Art Unit 2874 2883

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		5,446,754	08/29/1995	Jewell, et al.			
		5,465,263	11/07/1995	Bour, et al.			
		5,475,701	12/12/1995	Hibbs-Brenner			
		5,493,577	02/1996	Choquette, et al.			
		5,497,390	03/05/1996	Tanaka, et al.			
		5,513,202	04/30/1996	Kobayashi, et al.			
		5,530,715	06/25/1996	Shieh, et al.			
		5,555,255	09/10/1996	Kock, et al.			
		5,557,626	09/17/1996	Grodinski, et al.			
		5,561,683	10/01/1996	Kwon			
		5,567,980	10/22/1996	Holonyak, Jr. et al.			
		5,568,498	10/22/1996	Nilsson			
		5,568,499	10/22/1996	Lear			
		5,574,738	11/12/1996	Morgan			
		5,581,571	12/1996	Holonyak, Jr. et al.			
		5,586,131	12/17/1996	Ono, et al.			
		5,590,145	12/31/1996	Nitta			
		5,598,300	01/28/1997	Magnusson, et al.			
		5,606,572	02/25/1997	Swirhun, et al.			
		5,625,729	04/29/1997	Brown			
		5,642,376	06/24/1997	Olbright, et al.			
		5,645,462	07/08/1997	Banno, et al.			
		5,646,978	07/08/1997	Kem, et al.			
		5,648,978	07/15/1997	Sakata			
		5,679,963	10/21/1997	Klem, et al.			
		5,692,083	11/25/1997	Bennett			
		5,696,023	12/09/1997	Holonyak, Jr., et al.			
		5,699,373	12/16/1997	Uchida, et al.			
		5,712,188	01/27/1998	Chu, et al.			
		5,726,805	03/10/1998	Kaushik, et al.			
		5,727,013	03/10/1998	Botez, et al.			
		5,727,014	03/10/1998	Wang, et al.			
EXAMINER		DATE CONSIDERED					
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U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>W</i>		5,774,487	06/30/1998	Morgan			
<i>W</i>		5,778,018	07/07/1998	Yoshikawa, et al.			
<i>W</i>		5,781,575	07/14/1998	Nilsson			
<i>W</i>		5,784,399	07/21/1998	Sun			
<i>W</i>		4,790,733	08/04/1998	Smith, et al.			
<i>W</i>		5,805,624	09/08/1998	Yang, et al.			
<i>W</i>		5,818,066	10/06/1998	Duboz			
<i>W</i>		5,828,684	10/27/1998	Van de Walle			
<i>W</i>		5,838,705	11/17/1998	Shieh, et al.			
<i>W</i>		5,838,715	11/17/1998	Corzine, et al.			
<i>W</i>		5,892,784	04/16/1999	Tan, et al.			
<i>W</i>		5,892,727	04/06/1999	Tan, et al.			
<i>W</i>		5,896,408	04/20/1999	Corzine, et al.			
<i>W</i>		5,901,166	05/04/1999	Nitta, et al.			
<i>W</i>		5,903,588	05/1999	Guenter, et al.			
<i>W</i>		5,903,589	05/1999	Jewell			
<i>W</i>		5,903,590	05/11/1999	Hadley, et al.			
<i>W</i>		5,908,408	06/1999	McGary, et al.			
<i>W</i>		5,936,266	08/10/1999	Holonyak, Jr. et al.			
<i>W</i>		5,940,422	08/17/1999	Johnson			
<i>W</i>		5,953,362	09/14/1999	Pamulapati, et al.			
<i>W</i>		5,978,401	11/02/1999	Morgan			
<i>W</i>		5,978,408	11/1999	Thornton			
<i>W</i>		5,995,531	11/30/1999	Gaw, et al.			
<i>W</i>		6,002,705	12/14/1999	Thornton			
<i>W</i>		6,008,675	12/28/1999	Handa			
<i>W</i>		6,014,395	01/11/2000	Jewell			
<i>W</i>		6,043,104	03/28/2000	Uchida, et al.			
<i>W</i>		6,046,065	04/04/2000	Goldstein, et al.			
<i>W</i>		6,055,262	04/25/2000	Cox, et al.			
<i>W</i>		6,052,398	04/18/2003	Brillouet, et al.			
<i>W</i>		6,060,743	05/09/2000	Sugiyama, et al.			
EXAMINER	<i>Ryan J. L. 106</i>		DATE CONSIDERED <i>6/26/05</i>				

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.








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	Filing Date 02/17/2004	Group Art Unit 2874 2885

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>Dr</i>		6,078,601	06/20/2000	Smith			
<i>Dr</i>		6,086,263	07/11/2000	Selli, et al.			
<i>Dr</i>		6,133,590	10/17/2000	Ashley, et al.			
<i>Dr</i>		6,144,682	11/07/2000	Sun			
<i>Dr</i>		6,154,480	11/28/2000	Magnusson, et al.			
<i>Dr</i>		6,185,241	02/06/2001	Sun			
<i>Dr</i>		6,191,890	02/20/2001	Baets, et al.			
<i>Dr</i>		6,208,681	03/27/2001	Thorton			
<i>Dr</i>		6,212,312	04/03/2001	Grann, et al.			
<i>Dr</i>		6,238,944	05/29/2001	Floyd			
<i>Dr</i>		6,269,109	07/31/2001	Jewell			
<i>Dr</i>		6,297,068	10/02/2001	Thornton			
<i>Dr</i>		6,302,596	10/16/2001	Cohen, et a.			
<i>Dr</i>		6,339,496	01/15/2002	Koley, et al.			
<i>Dr</i>		6,369,403	04/09/2002	Holonyak, Jr.			
<i>Dr</i>		6,372,533	04/16/2002	Jayaraman, et al.			
<i>Dr</i>		6,392,257	05/21/2002	Ramdani, et al.			
<i>Dr</i>		6,410,941	06/25/2002	Taylor, et al.			
<i>Dr</i>		6,411,638	06/25/2002	Johnson, et al.			
<i>Dr</i>		6,427,066	07/30/2002	Grube			
<i>Dr</i>		6,455,879	09/24/2002	Ashley, et al.			
<i>Dr</i>		6,459,709	10/01/2002	Lo, et al.			
<i>Dr</i>		6,459,713	10/01/2002	Jewell			
<i>Dr</i>		6,462,360	10/08/2002	Higgins, Jr. et al.			
<i>Dr</i>		6,472,694	10/29/2002	Wilson, et al.			
<i>Dr</i>		6,477,285	11/05/2002	Shanley			
<i>Dr</i>		6,487,230	11/26/2002	Boucart, et al.			
<i>Dr</i>		6,487,231	11/26/2002	Boucart, et al.			
<i>Dr</i>		6,490,311	12/03/2002	Boucart, et al.			
<i>Dr</i>		6,493,371	12/10/2002	Boucart, et al.			
<i>Dr</i>		6,493,372	12/10/2002	Boucart, et al.			
<i>Dr</i>		6,493,373	12/10/2002	Boucart, et al.			
EXAMINER <i>Ryan Jg 86</i>		DATE CONSIDERED <i>6/21/05</i>					
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>	Docket number (Optional) 15436.442.6	Application Number 10/781,446
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	Filing Date 02/17/2004	Group Art Unit 2874 2883

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>[Signature]</i>		6,496,621	12/17/2002	Kathman, et al.			
<i>[Signature]</i>		6,498,358	12/24/2002	Lach, et al.			
<i>[Signature]</i>		6,501,973	12/31/2002	Foley, et al.			
<i>[Signature]</i>		6,515,308	02/04/2003	Kneissl, et al.			
<i>[Signature]</i>		6,535,541	03/18/2003	Boucart, et al.			
<i>[Signature]</i>		6,542,531	04/01/2003	Sirbu, et al.			
<i>[Signature]</i>		6,567,435	05/20/2003	Scott, et al.			
<i>[Signature]</i>		6,536,959	03/25/2003	Kuhn, et al.			

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*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>[Signature]</i>		2001/0004414	06/21/2001	Kuhn, et al.			
<i>[Signature]</i>		2003/0072526	04/17/2003	Kathman, et al.			


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	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
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EXAMINER <i>[Signature]</i>	DATE CONSIDERED <i>6/21/05</i>
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INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>	Docket number (Optional) 15436.442.6	Application Number 10/781,446
	Applicant(s) Bo Su Chen	
	Filing Date 02/17/2004	Group Art Unit 2874 2983

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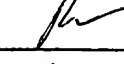
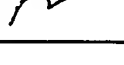
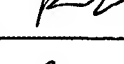
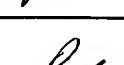
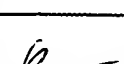

EXAMINER <i>Roger J. [Signature]</i>	DATE CONSIDERED <i>6/21/06</i>
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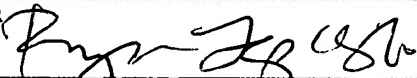
INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>	Docket number (Optional) 15436.442.6	Application Number 10/781,446
	Applicant(s) Bo Su Chen	
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